

Radiation	Type	Technology	Electrodes
Red	Point Source	AlInGaP/GaAs	N (cathode) up

<p>PS-03</p>	typ. dimensions ( $\mu\text{m}$ )	
	<u>typ. thickness</u> 250 ( $\pm 20$ ) $\mu\text{m}$	
	<u>cathode</u> gold alloy, 1.5 $\mu\text{m}$	
	<u>anode</u> gold alloy, 0.5 $\mu\text{m}$	

### Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward current (DC)		$I_F$			35	mA

### Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 5 \text{ mA}$	$V_F$		1.85	2.4	V
Reverse voltage	$I_R = 10 \mu\text{A}$	$V_R$	5			V
Radiant power*	$I_F = 5 \text{ mA}$	$\Phi_e$	100	200		$\mu\text{W}$
Luminous intensity*	$I_F = 5 \text{ mA}$	$I_V$	5	7		mcd
Peak wavelength	$I_F = 5 \text{ mA}$	$\lambda_p$	645	655	665	nm
Spectral bandwidth at 50%	$I_F = 5 \text{ mA}$	$\Delta\lambda_{0.5}$		20		nm
Switching time	$I_F = 5 \text{ mA}$	$t_r, t_f$		40/30		ns

\*Measured on bare chip on TO-18 header with *EPIGAP* equipment

### Labeling

Type	Lot N°	$I_V(\text{typ})$ [mcd]	$V_F(\text{typ})$ [V]	Quantity
ELC-650-29-50				

**Packing:** Chips on adhesive film with wire-bond side on top